

### **Amendments to the Specification**

- 1) Please insert the following subtitle at page 1, below the title:

#### **Background**

- 2) Please replace the paragraph at page 2, line 9, with the following:

The use of carbon-containing volatile silazanes, azidosilazanes, and aminosilanes as silicon nitride precursors has been proposed in order to solve the problems cited above (refer, for example, to ~~non-patent references 1 and 2~~ Grow et al., Mater. Lett. 23, 187, 1995, and Levy et al., J. Mater. Res., 11, 1483, 1996). However, these silicon nitride precursors, whether used by themselves or in combination with ammonia, result in the incorporation of SiC and/or large amounts of carbon in the silicon nitride film product.

- 3) Please delete the text at page 2, lines 15 – 18.

- 4) Please delete the subtitle at page 2, line 20.

- 5) Please insert the following subtitle and text at page 2, line 21:

#### **Summary**

The invention includes methods to achieve the desired results, as described, but is not limited to the various embodiments disclosed.

- 6) Please delete the subtitle at page 2, line 27.

- 7) Please insert the following subtitle and text at page 2, line 28:

#### **Brief Description of the Drawings**

For a further understanding of the nature and objects for the present invention, reference should be made to the following detailed description, taken in conjunction with the accompanying drawings, in which like elements are given the same or analogous reference numbers and wherein:

- Figure 1 illustrates a block diagram of one type of apparatus for producing silicon nitride films;
- Figure 2 illustrates a block diagram of another type of apparatus for producing silicon nitride films;
- Figure 3 illustrates a block diagram of a precursor feed gas system which uses a bubbler;

- Figure 4 illustrates a block diagram of a precursor feed gas system which uses a vaporizer;
- Figure 5 illustrates a graphical representation of the relationship between the CVD reaction temperature and the growth rate of a silicon nitride film;
- Figure 6 illustrates a graphical representation of the relationship between the intensity ratio of the two main peaks for TSA and reaction temperature; and
- Figure 7 illustrates a graphical representation between a CVD reaction temperature and a step coverage ratio for silicon nitride films.

8) Please insert the following subtitle and text after the above-inserted paragraphs:

**Description of Preferred Embodiments**

The invention includes methods for producing a silicon nitride film, as described above.

9) Please delete the text at page 13, line 6 through line 20.

10) Please insert the following paragraph at page 13, line 6:

It will be understood that many additional changes in the details, materials, steps and arrangement of parts, which have been herein described in order to explain the nature of the invention, may be made by those skilled in the art within the principle and scope of the invention as expressed in the appended claims. Thus, the present invention is not intended to be limited to the specific embodiments in the examples given above.

11) Please replace the subtitle at page 14, line 1, with the following text:

~~Claims~~ What is claimed is: